

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings of claims in the application:

Listing of Claims:

1 1. (Original) An optical transmission module comprising:
2 a driver IC chip which drives a semiconductor laser device;
3 a first insulation plate which is placed adjacent to the driver IC chip and has the
4 semiconductor laser device mounted thereon;
5 a coupling optical component which is place adjacent to the first insulation plate
6 and is used to emit an optical signal from the semiconductor laser device into an optical fiber;
7 and
8 a second insulation plate which is placed adjacent to the first insulation plate and
9 has a thin film inductor element and a thin film resistor element mounted thereon;
10 wherein the driver IC chip, the first insulation plate, the coupling optical
11 component, and the second insulation plate are contained in a package; and
12 wherein the first insulation plate and the second insulation plate are connected by
13 using a bonding wire or ribbon so that a bias current is supplied to the semiconductor laser
14 device via the thin film inductor element and the thin film resistor element which are connected
15 in parallel.

1 2. (Original) An optical transmission module according to claim 1 wherein a
2 terminal of the driver IC chip is connected with an electrode on the first insulation plate by using
3 a bonding wire or ribbon.

1 3. (Original) An optical transmission module according to claim 1 wherein a
2 resonant frequency in a resonant circuit composed of grounding capacitance of the thin film
3 inductor element on the second insulation plate and an inductance of the bonding wire is not
4 lower than 8 GHz.

1 4. (Original) An optical transmission module according to claim 1 wherein
2 the driver IC chip is a current drive type.

1 5. (Original) An optical transmission module according to claim 2 wherein
2 the driver IC chip is a current drive type.

6. (Canceled)

1 7. (Currently amended) An optical transmission module according to claim
2 6 wherein a bias current is supplied to a semiconductor laser device via a thin film inductor
3 element and a thin film resistor element which are connected in parallel, wherein a first
4 insulation plate having the semiconductor laser device mounted thereon and a second insulation
5 plate having the thin film inductor element and the thin film resistor element formed thereon are
6 respectively formed as separate insulation plates and an electrode formed on the first insulation
7 plate is connected via a bonding wire or ribbon with one end pad of the thin film inductor
8 element and the thin film resistor element which are connected in parallel.

1 8. (Original) An optical transmission module according to claim 7 wherein a
2 resonant frequency in a resonant circuit composed of grounding capacitance of the thin film
3 inductor element on the second insulation plate and an inductance of the bonding wire is not
4 lower than 8 GHz.

1 9. (Original) An optical transmission module according to claim 7 wherein a
2 driver IC chip to drive the semiconductor laser device is placed adjacent to the first insulation
3 plate and a terminal of the driver IC chip is connected with an electrode on the first insulation
4 plate by using bonding a wire or ribbon.

1 10. (Original) An optical transmission module according to claim 9 wherein
2 the driver IC chip is a current drive type.